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Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

ON Semiconductor
MMBT2132T3

For any questions, you can email us directly:
sales@integrated-circuit.com

MMBT2132T3

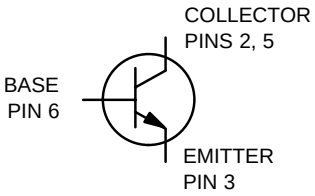
General Purpose Transistors

NPN Bipolar Junction Transistor

ON Semiconductor®

http://onsemi.com

0.7 AMPS
30 VOLTS − $V_{(BR)CEO}$
342 mW



TSOP−6/SC−74
CASE 318F
STYLE 2

Features

- Pb−Free Package is Available

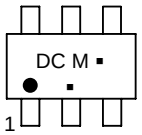
MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	30	V
Collector−Base Voltage	V_{CBO}	40	V
Emitter−Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	700	mA
Base Current	I_B	350	mA
Total Power Dissipation @ T_C = 25°C Total Power Dissipation @ T_C = 85°C Thermal Resistance, Junction−to−Ambient (Note 1)	P_D P_D $R_{\theta JA}$	342 178 366	mW mW °C/W
Total Power Dissipation @ T_C = 25°C Total Power Dissipation @ T_C = 85°C Thermal Resistance, Junction−to−Ambient (Note 2)	P_D P_D $R_{\theta JA}$	665 346 188	mW mW °C/W
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Minimum FR−4 or G−10 PCB, Operating to Steady State.
2. Mounted onto a 2″ square FR−4 Board (1″ sq 2 oz Cu 0.06″ thick single sided), Operating to Steady State.

MARKING DIAGRAM



DC = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2132T3	TSOP−6	10,000/Tape & Reel
MMBT2132T3G	TSOP−6 (Pb−Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT2132T3

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−Base Breakdown Voltage	(I_C = 100 μAdc)	$V_{(BR)CBO}$	40	−	−	Vdc
Collector−Emitter Breakdown Voltage	(I_C = 10 mAdc)	$V_{(BR)CEO}$	30	−	−	Vdc
Emitter−Base Breakdown Voltage	(I_E = 100 μAdc)	$V_{(BR)EBO}$	5.0	−	−	Vdc
Collector Cutoff Current	(V_{CB} = 25 Vdc, I_E = 0 Adc) (V_{CB} = 25 Vdc, I_E = 0 Adc, T_A = 125°C)	I_{CBO}	− −	− −	1.0 10	μAdc
Emitter Cutoff Current	(V_{EB} = 5.0 Vdc, I_C = 0 Adc)	I_{EBO}	−	−	10	μAdc
ON CHARACTERISTICS						
DC Current Gain	(V_{CE} = 3.0 Vdc, I_C = 100 mAdc)	h_{FE}	150	−	−	Vdc
Collector−Emitter Saturation Voltage	(I_C = 500 mAdc, I_B = 50 mAdc)	$V_{CE(sat)}$	−	−	0.25	Vdc
Collector−Emitter Saturation Voltage	(I_C = 700 mAdc, I_B = 70 mAdc)	$V_{CE(sat)}$	−	−	0.4	Vdc
Base−Emitter Saturation Voltage	(I_C = 700 mAdc, I_B = 70 mAdc)	$V_{BE(sat)}$	−	−	1.1	Vdc
Collector−Emitter Saturation Voltage	(I_C = 700 mAdc, V_{CE} = 1.0 Vdc)	$V_{BE(on)}$	−	−	1.0	Vdc

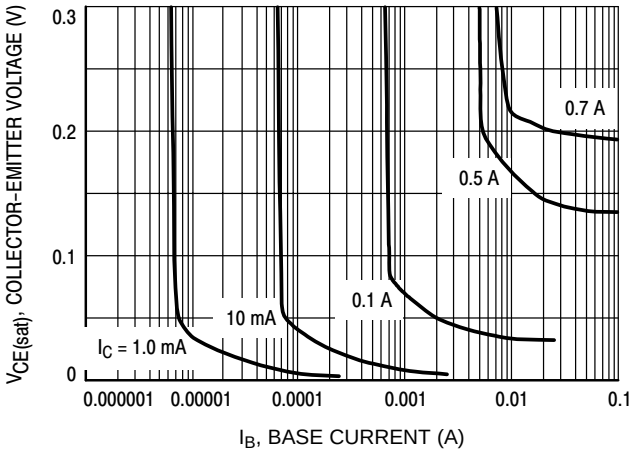


Figure 1. Collector Saturation Region

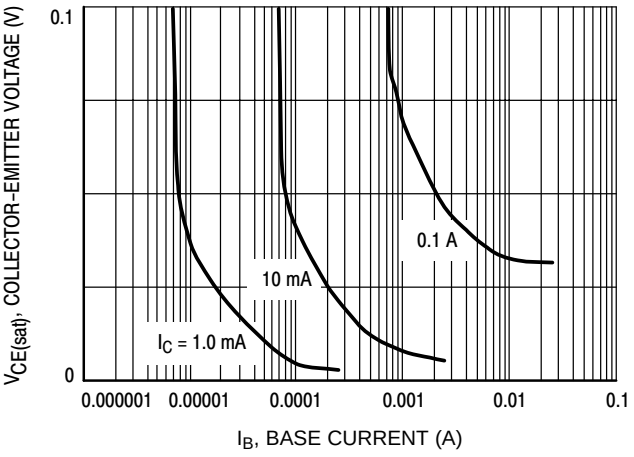


Figure 2. Collector Saturation Region

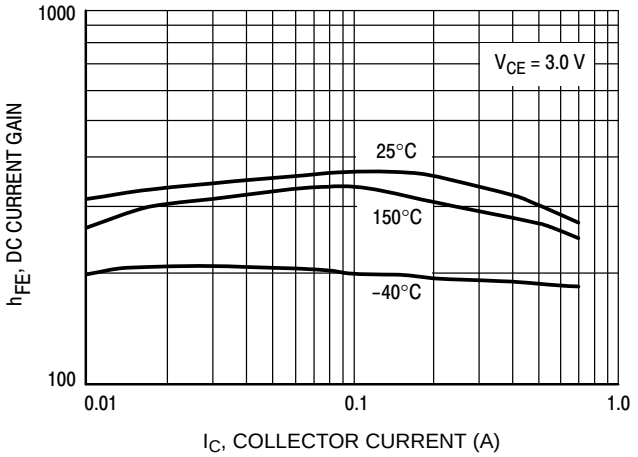


Figure 3. DC Current Gain

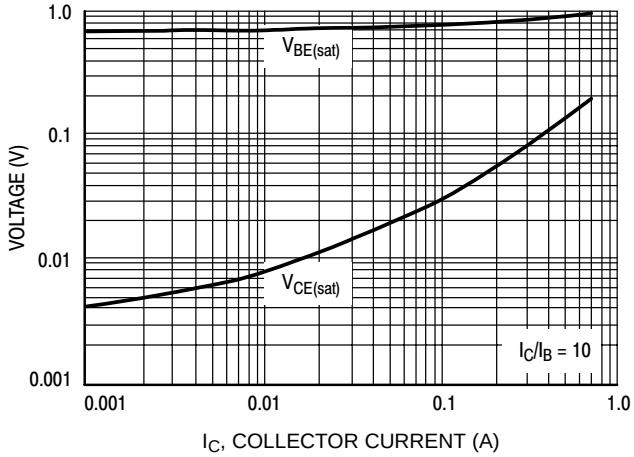


Figure 4. “ON” Voltages

MMBT2132T3

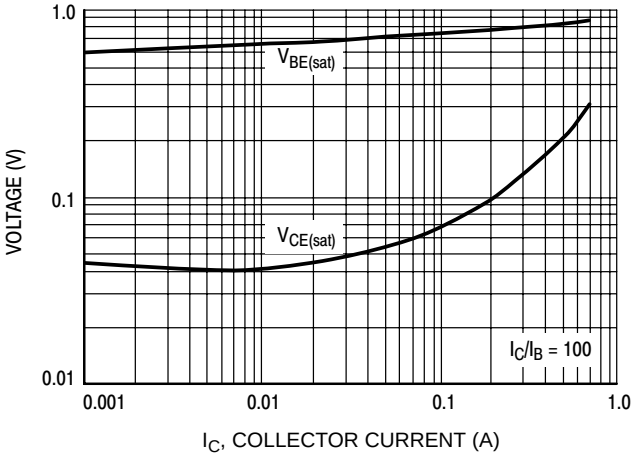


Figure 5. “ON” Voltages

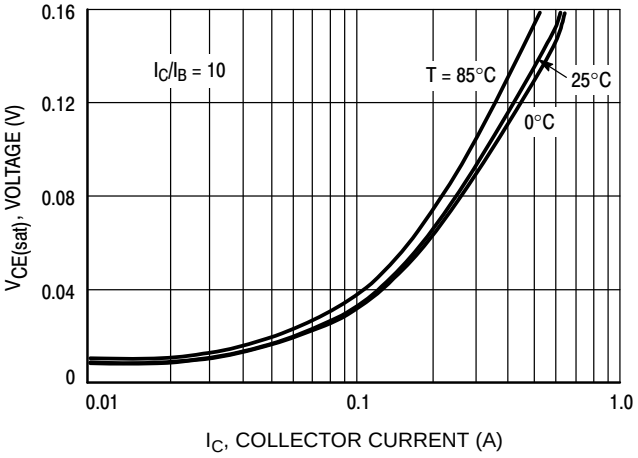


Figure 6. Collector−Emitter Saturation Voltage

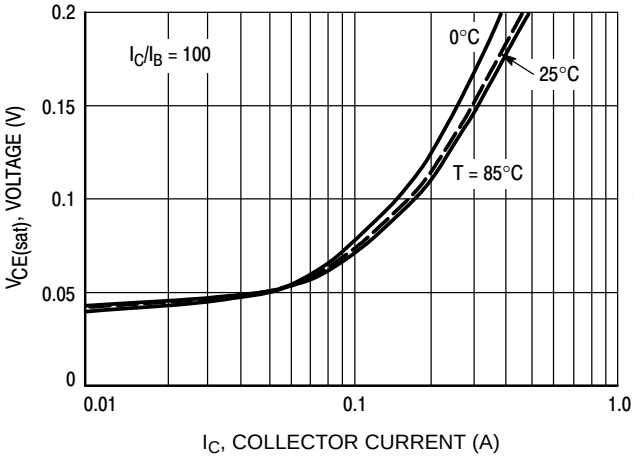


Figure 7. Collector−Emitter Saturation Voltage

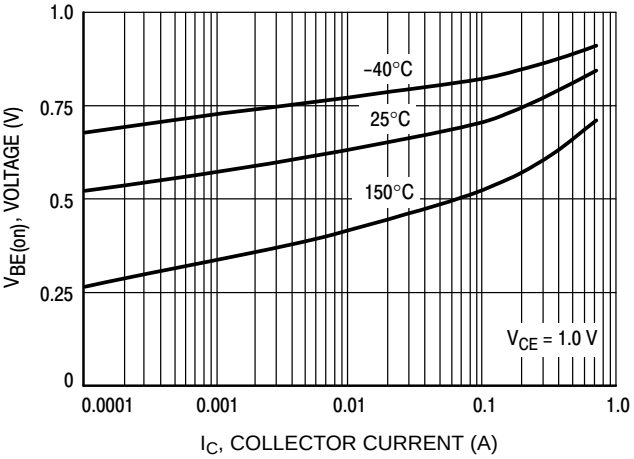


Figure 8. $V_{BE(on)}$ Voltage

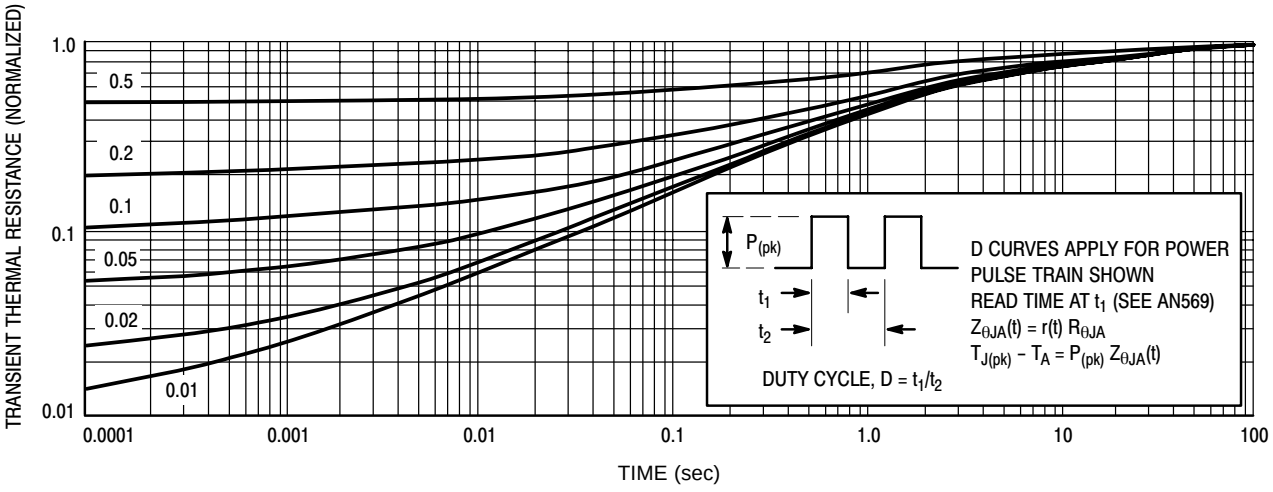
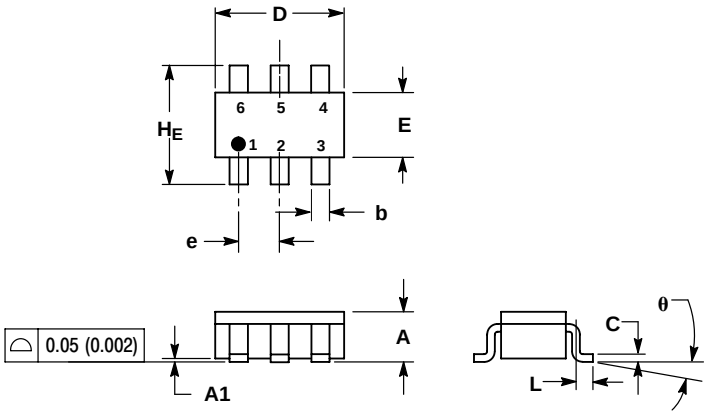


Figure 9. Thermal Response Curve

MMBT2132T3

PACKAGE DIMENSIONS

SC−74
CASE 318F−05
ISSUE L

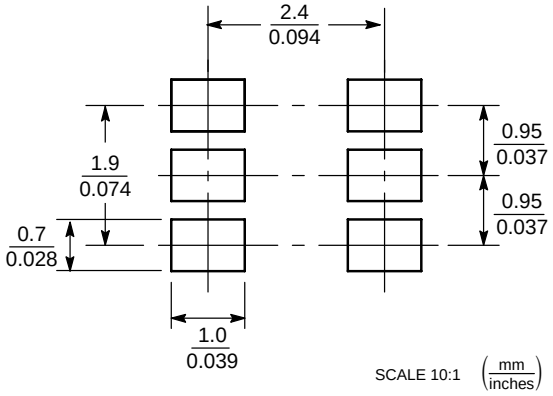


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F−01, −02, −03 OBSOLETE. NEW STANDARD 318F−04.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	–	10°	0°	–	10°

STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

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